BAW56L, SBAW56L

Dual Switching Diode Common Anode

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	70	V
Forward Current	١ _F	200	mA
Forward Surge Current (60 Hz @ 1 cycle)	I _{FSM}	2.0	A
Non–Repetitive Peak Forward Current t = 1 μ s (Note 3)	I _{FSM}	4.0	A
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I _{FRM}	500	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$ Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^{\circ}C$ Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

3. Square Wave; $T_i = 25^{\circ}C$.

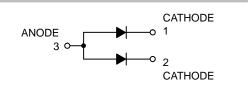


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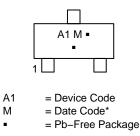
www.onsemi.com







MARKING DIAGRAM



(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BAW56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SBAW56LT1G	SOT–23 (Pb–Free)	3,000 / Tape & Reel
BAW56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SBAW56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

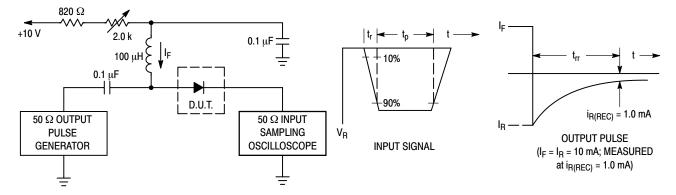
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL	CHARACTERISTICS (T _A =	= 25°C unless otherwise noted)	(Each Diode)
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Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage $(I_{(BR)} = 100 \ \mu A)$	V _(BR)	70	_	V
Reverse Voltage Leakage Current $(V_R = 25 \text{ V}, \text{ T}_J = 150^{\circ}\text{C})$ $(V_R = 70 \text{ V})$ $(V_R = 70 \text{ V}, \text{ T}_J = 150^{\circ}\text{C})$	IR	- - -	30 2.5 50	μΑ
Diode Capacitance (V _R = 0 V, f = 1.0 MHz)	C _D	_	2.0	pF
Forward Voltage $(I_F = 1.0 \text{ mA})$ $(I_F = 10 \text{ mA})$ $(I_F = 50 \text{ mA})$ $(I_F = 150 \text{ mA})$	V _F	- - - -	715 855 1000 1250	mV
Reverse Recovery Time (I _F = I _R = 10 mA, I _{R(REC)} = 1.0 mA) (Figure 1) R _L = 100 Ω	t _{rr}	_	6.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA. 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA. 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

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Curves Applicable to Each Cathode

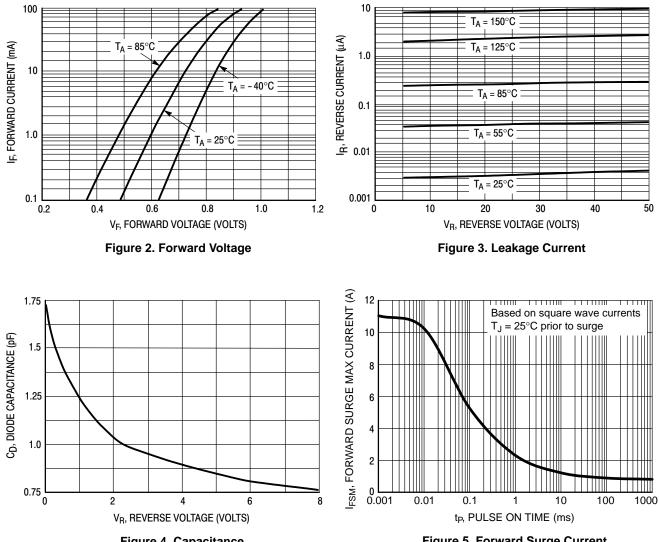


Figure 4. Capacitance

Figure 5. Forward Surge Current





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